

CIGS - *TORRENT* VAPOR SOURCE

VPT Vapor Source Specifications (for metal evaporation)

Description	Value
Source dimension	
L(mm) × W(mm) × H(mm)	2220 × 450 × 740
or L(mm) × W(mm) × H(mm)	1500 × 450 × 740
Deposition method	In-line thermal evaporation
Deposition type	Top - down
Source exit slit to substrate distance(adjustable, mm)	300 -500
Substrate width (mm)	up to 1200
Source uniformity (source center to ± 600mm)	< ±5%
Static evaporation rate	
g/min	0.8 - 6
nm/s	2 - 15
Dynamic deposition rate (nm m/min)	36 - 270
Evaporation rate stability	±2%
Source operating temperature - maximum (°C)	1450
Source temperature stability, crucible (°C)	±1
Source crucible capacity (cm ³)	2400/4800
Source power consumption (kW)	80 - 100

